IN THE SPECIFICATION

Please remove the section starting on page 7 of the specification, line 7, and ending on page 8, line 22.

~~Embodiments of the invention will now be described in a non-limiting way.~~

~~A method of fabricating a semiconductor device in accordance with an embodiment of the invention includes: preparing a semiconductor substrate having a first contact pad and a second contact pad; forming a first insulating film on the substrate; etching the first insulating film to form a contact and a groove-shaped bit line pattern exposing the first contact pad and the second contact pad; simultaneously forming a contact plug and a bit line in the contact and the bit line pattern, respectively, the contact plug and the bitline having upper surfaces that are coplanar; and forming a bottom electrode of a capacitor that connects to the first contact pad.~~

~~A method of fabricating a semiconductor device in accordance with another embodiment of the invention includes: forming a first insulating film having a storage node contact pad and a bitline contact pad on a semiconductor substrate; forming a second insulating film having a bit line contact exposing the bitline contact pad on the first insulating film; forming a bitline contact plug on the bit line contact; forming a third insulating film on the substrate; etching the second and third insulating films to form a groove-shaped bit line pattern and a storage node contact; simultaneously forming a bit line and a contact plug in the bitline pattern and the storage node contact, respectively, the bitline and the contact plug having upper surfaces that are coplanar; forming a fourth insulating film and a fifth insulating film on the semiconductor substrate; forming an opening exposing the contact plug by etching the fourth insulating film and the fifth insulating film; removing the exposed contact plug to expose the storage node contact; forming a storage node contacted with the storage node contact pad in the opening including the exposed storage node contact; and removing the fifth insulating film.~~

~~A method for fabricating a semiconductor device in accordance with yet another embodiment of the invention includes: forming a first insulating film having a storage node contact pad and a bitline contact pad on a semiconductor substrate; forming a second insulating film having a bit line contact exposing the bitline contact pad on the first insulating film; forming a bitline contact plug in the bit line contact; forming a third insulating film on~~

~~the substrate; etching the second and third insulating films to form a groove-shaped bit line pattern and the storage node contact; simultaneously forming a bit line and a contact plug in the bitline pattern and the storage node contact, respectively, the bitline and the contact plug having upper surfaces that are coplanar; forming a fourth insulating film having an opening exposing the contact plug on the semiconductor substrate; and forming a metal electrode in contact with the contact plug through the opening on the fourth insulating film.~~

~~A semiconductor device according to an embodiment of the invention includes: a semiconductor substrate having a bitline contact pad and a storage node contact pad; a first insulating film that includes a groove-shaped bit line pattern exposing the bitline contact pad and a storage node contact exposing the storage node contact pad, the bitline pattern and the storage node contact having upper portions that are coplanar; a bit line formed on the bit line pattern; a second insulating film having an opening exposing the storage node contact; and a bottom electrode of the capacitor in contact with the storage node contact pad, formed in the storage node contact and protruding from the second insulating film.~~

~~A semiconductor device according to another embodiment of the invention includes: a semiconductor substrate having a bitline contact pad and a storage node contact pad; a first insulating film that includes a groove-shaped bit line pattern exposing the bitline contact pad and a storage node contact exposing the storage node contact pad, the bitline pattern and the storage node contact having upper portions that are coplanar; a bit line formed on the bit line pattern; a contact plug formed in the storage node contact; a second insulating film having an opening exposing the contact plug; and a bottom electrode of a capacitor formed on the second insulating film, in contact with the exposed contact plug through the opening.~~